

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A method for manufacturing a ceramic film, the method comprising:

preparing a substrate including an electrode made of a platinum group element;

applying a ceramic material to ~~a substrate~~ the substrate;

rotating the substrate at a first speed for a first time;

rotating the substrate at a second speed lower than the first speed for a second ~~time~~
time, the second time being longer than the first time;

rotating the substrate at a third speed higher than the second speed for a third time;

and

forming the ceramic film including a perovskite structure by a heat treatment.

2. (Previously Presented) The method as defined in claim 1, the third speed being higher than the first speed.

3. (Previously Presented) The method as defined in claim 1, further comprising:
drying the ceramic material coated on the substrate after rotating the substrate at the third speed.

4. (Previously Presented) The method as defined in claim 3, the drying the ceramic material being performed by blowing gas onto the ceramic material.

5. (Previously Presented) The method as defined in claim 1, the ceramic material including at least one of a sol-gel raw material and an MOD raw material, the sol-gel raw material including at least one of a hydrolysate and a polycondensate of the complex oxide, the MOD raw material including constituent elements of the complex oxide in an organic solvent.

6. (Currently Amended) The method as defined in claim 1, the ~~substrate including an electrode layer~~ platinum group element including platinum, ruthenium, rhodium, palladium, osmium or iridium,

the ceramic material being applied on the electrode in the applying the ceramic material.

7. (Withdrawn) A ceramic film obtained by the ceramic material coating method as defined by claim 1.

8. (Withdrawn) A ceramic film obtained by the ceramic material coating method as defined by claim 2.

9. (Withdrawn) A ceramic film obtained by the ceramic material coating method as defined by claim 3.

10. (Withdrawn) A ceramic film obtained by the ceramic material coating method as defined by claim 4.

11. (Previously Presented) The method as defined in claim 1, the first time being shorter than the third time.

12. (Previously Presented) The method as defined in claim 1, the ceramic material including at least one of Bi, Ti, La and Pb.

13. (Previously Presented) The method as defined in claim 1, the ceramic material including at least one of Si and Ge.

14. (Currently Amended) The method as defined in ~~claim 8,~~ claim 12, the ceramic material further including at least one of Si and Ge.

15. (Previously Presented) The method as defined in claim 1, the ceramic film including Pb, Zr, and Ti.

16. (Previously Presented) The method as defined in claim 1, the ceramic film including PZT, BiLaTiO, BiTiO or SrBiTaO.

17. (Previously Presented) A method for manufacturing a ferroelectric memory comprising the method as defined as claim 1.

18. (Previously Presented) A method for manufacturing a semiconductor device comprising the method as defined as claim 1.

19. (New) A method for manufacturing a ceramic film, the method comprising:
preparing a substrate including an electrode made of a platinum group element;
applying a ceramic material to the substrate;
rotating the substrate at a first speed for a first time;
rotating the substrate at a second speed lower than the first speed for a second time,
the second time being longer than the first time;
rotating the substrate at a third speed higher than the second speed for a third time,
blowing gas onto the ceramic material at a first temperature; and
heating the substrate by a hot plate at a second temperature,
the blowing and the heating being conducted simultaneously, and
the first temperature being lower than the second temperature.